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(54) Title: SHADOW RING KIT FOR PLASMA ETCH WAFER SINGULATION PROCESS

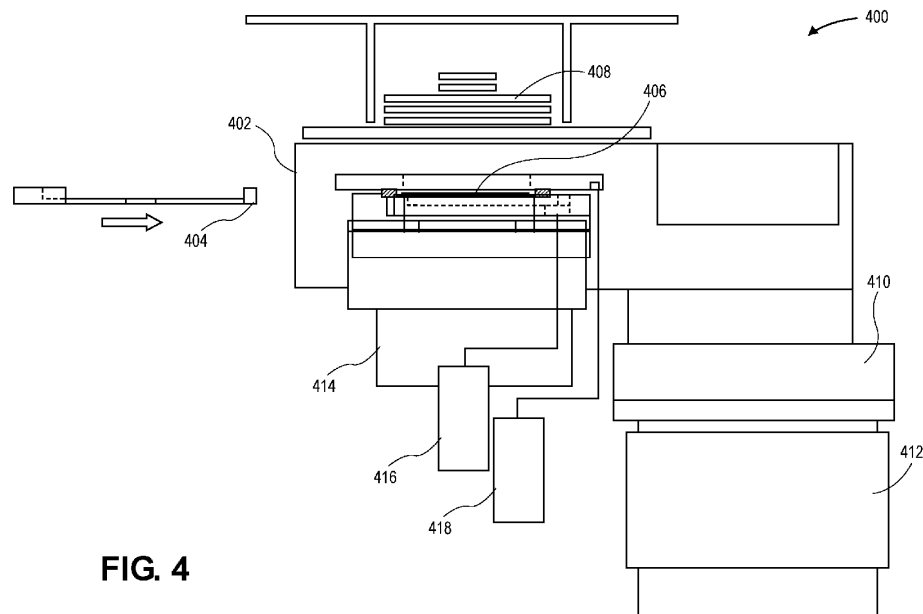


FIG. 4

(57) Abstract: Shadow ring kits and methods of dicing semiconductor wafers are described. In an example, an etch apparatus includes a chamber, and a plasma source within or coupled to the chamber. An electrostatic chuck is within the chamber, the electrostatic chuck including a conductive pedestal to support a substrate carrier sized to support a wafer having a first diameter. A shadow ring assembly is between the plasma source and the electrostatic chuck, the shadow ring assembly sized to process a wafer having a second diameter smaller than the first diameter.

[Continued on next page]

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